IN THE CLAIMS:

1-11 (Cancelled).

12. (original) A thin film-transistor manufacturing method comprising:

an opaque film step of forming an opaque film having a predetermined shape on a substrate:

an insulating film step of forming an insulating film on said substrate so as to cover said opaque film;

a source-and-drain-electrode forming step of forming a source electrode and a drain electrode which are made of metallic films having a predetermined line width and keeping a predetermined interval from each other on said formed insulating film;

a semiconductor-insulating-film-layer step of forming a semiconductor layer and a gate insulating film layer on said insulating film in order above said source electrode and said drain electrode;

a gate-electrode forming step of forming a metallic film for a gate electrode on said gate insulating film layer;

a pattern forming step of patterning said semiconductor layer, said gate insulating film layer, and said metallic film for a gate electrode and forming a protruded TFT portion having a thin-film-transistor-channel structure and in which said semiconductor layer and said gate insulating film layer are formed at said position of said gate electrode exceeding said protruded TFT portion; wherein

said source-and-drain-electrode forming step forms at least either of a source electrode and a drain electrode serving as a signal electrode so as to cross said protruded TFT portion formed in said pattern forming step.

13. (original) The thin-film-transistor manufacturing method according to Claim 12, wherein said pattern forming step pattern-forms said semiconductor layer, said gate insulating film layer, and said metallic film for a gate electrode in said same patterning step.

14. (original) The thin-film-transistor manufacturing method according to Claim 12, wherein said pattern forming step pattern-forms said semiconductor layer, said gate insulting film layer, and said metallic film for a gate electrode into almost said same shape.

15. - 18. (cancelled)